

NPN Epitaxial Planar Transistor

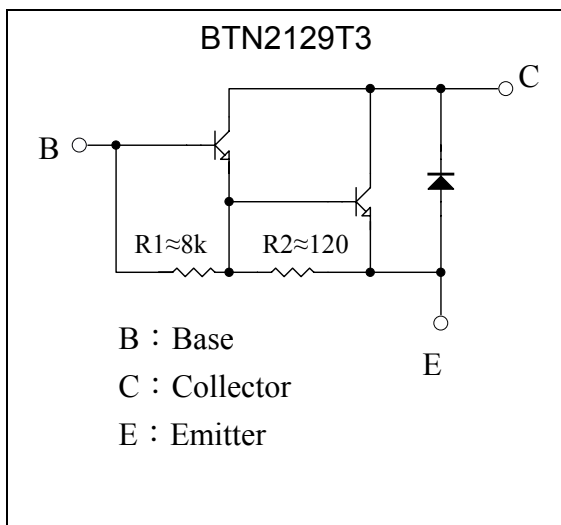
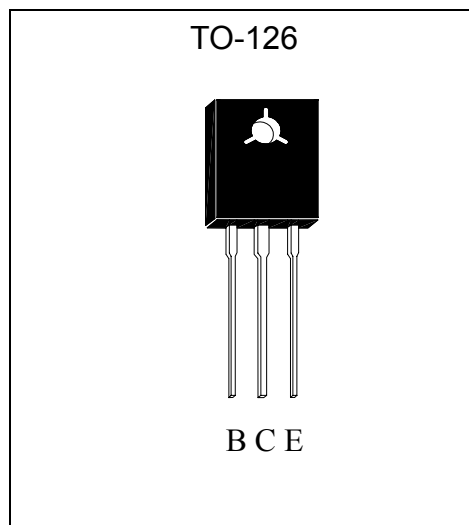
BTN2129T3

Description

The BTN2129T3 is a NPN Darlington transistor, designed for general purpose amplifier and low speed switching application.

Features:

- High current capability
- Low $V_{CE(SAT)}$
- High current gain
- Monolithic construction with built-in base-emitter shunt resistors

Equivalent Circuit**Outline**

**Absolute Maximum Ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	80	V
Collector-Emitter Voltage	V _{CE0}	50	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current (DC)	I _C	8	A
Collector Current (Pulse)	I _{CP}	12 *1	
Power Dissipation	Pd(T _A =25°C)	1	W
	Pd(T _C =25°C)	20	
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

Note : *1. Single Pulse Pw=100ms

Characteristics (Ta=25°C)

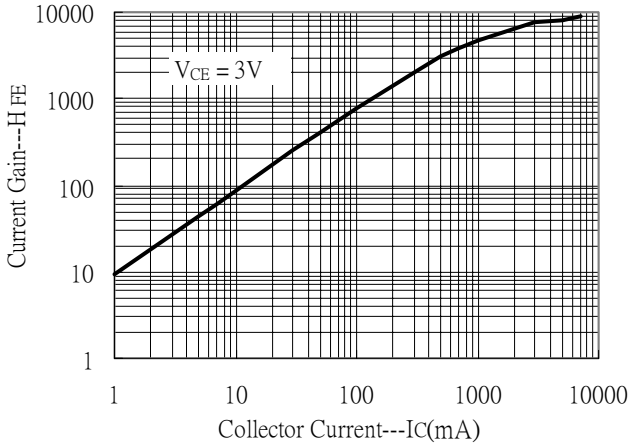
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CE0}	50	-	-	V	I _C =1mA, I _B =0
I _{CE0}	-	-	10	μA	V _{CE} =40V, I _E =0
I _{CB0}	-	-	10	μA	V _{CB} =80V, I _E =0
I _{EBO}	-	-	2	mA	V _{EB} =5V, I _C =0
*V _{CE(sat)} 1	-	-	1.3	V	I _C =3A, I _B =12mA
*V _{CE(sat)} 2	-	-	1.5	V	I _C =5A, I _B =20mA
*V _{BE(sat)}	-	-	2.1	V	I _C =3A, I _B =12mA
*V _{BE(on)} 1	-	-	2	V	V _{CE} =3V, I _C =3A
*V _{BE(on)} 2	-	-	2.1	V	V _{CE} =4V, I _C =4A
*h _{FE} 1	500	-	-	-	V _{CE} =3V, I _C =500mA
*h _{FE} 2	2	-	20	K	V _{CE} =3V, I _C =3A
*h _{FE} 3	2	-	-	K	V _{CE} =4V, I _C =4A

*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

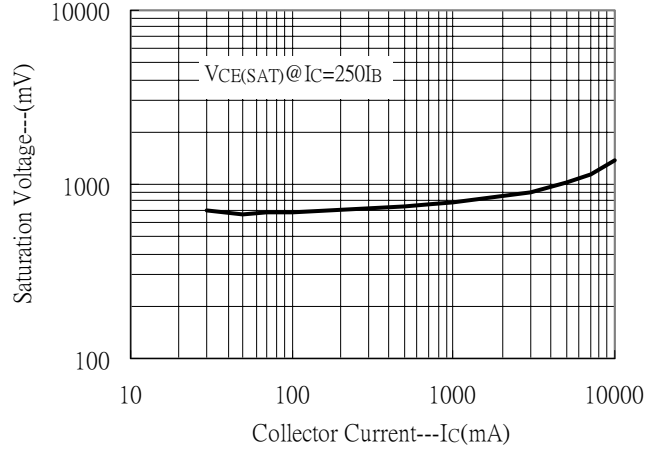


Characteristic Curves

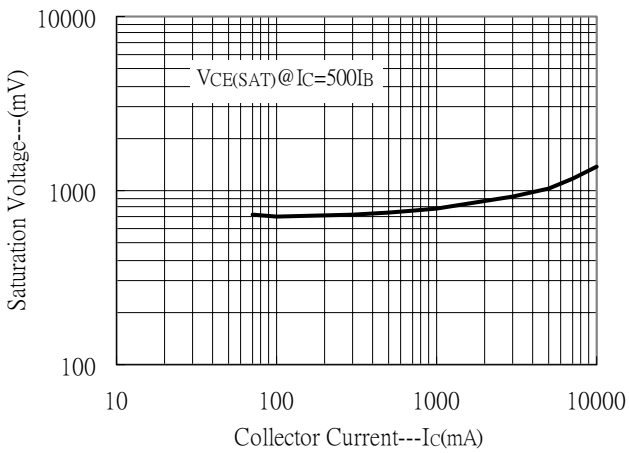
Current Gain vs Collector Current



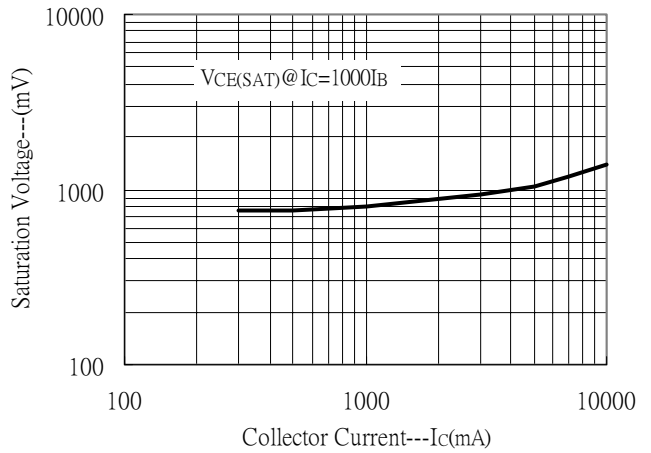
Saturation Voltage vs Collector Current



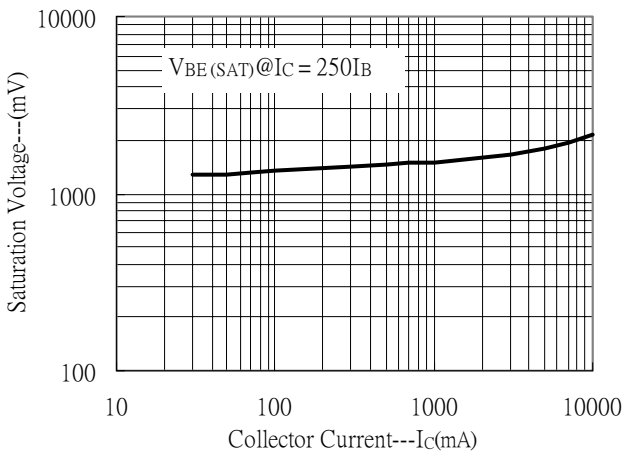
Saturation Voltage vs Collector Current



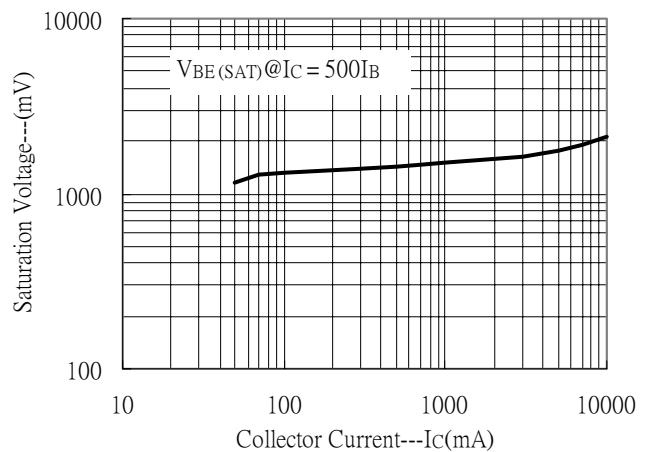
Saturation Voltage vs Collector Current



Saturation Voltage vs Collector Current



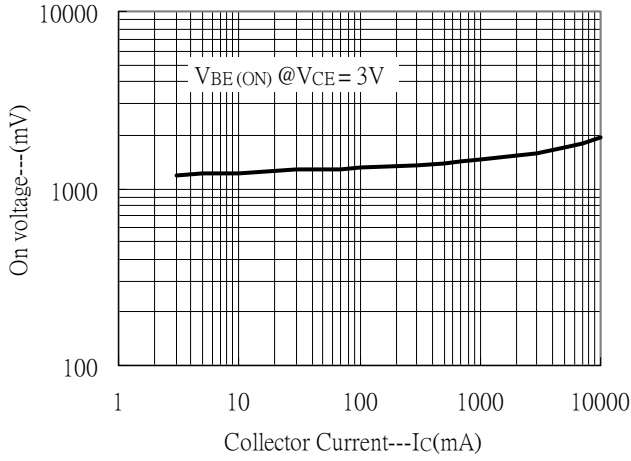
Saturation Voltage vs Collector Current



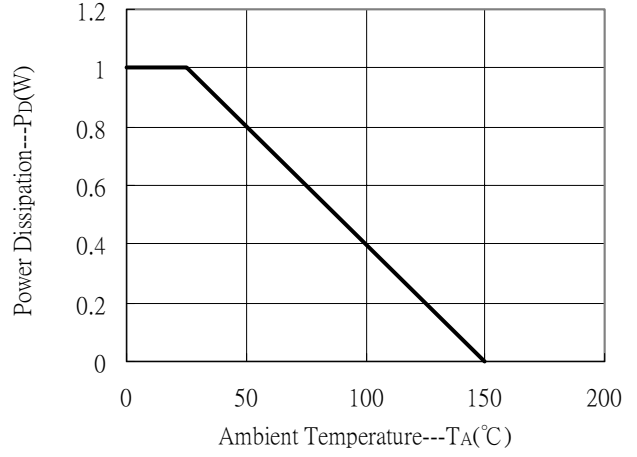


Characteristic Curves(Cont.)

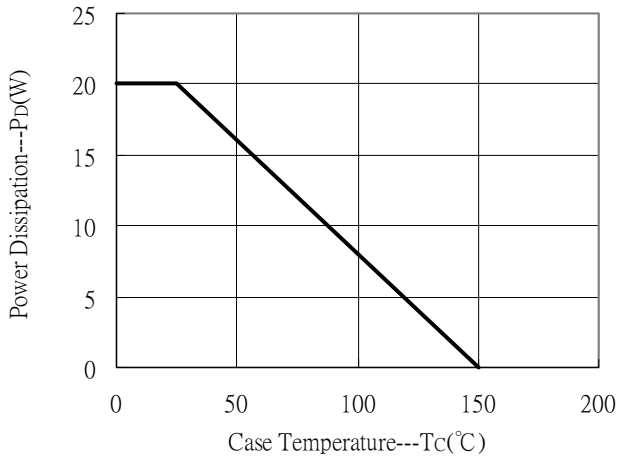
On voltage vs Collector Current



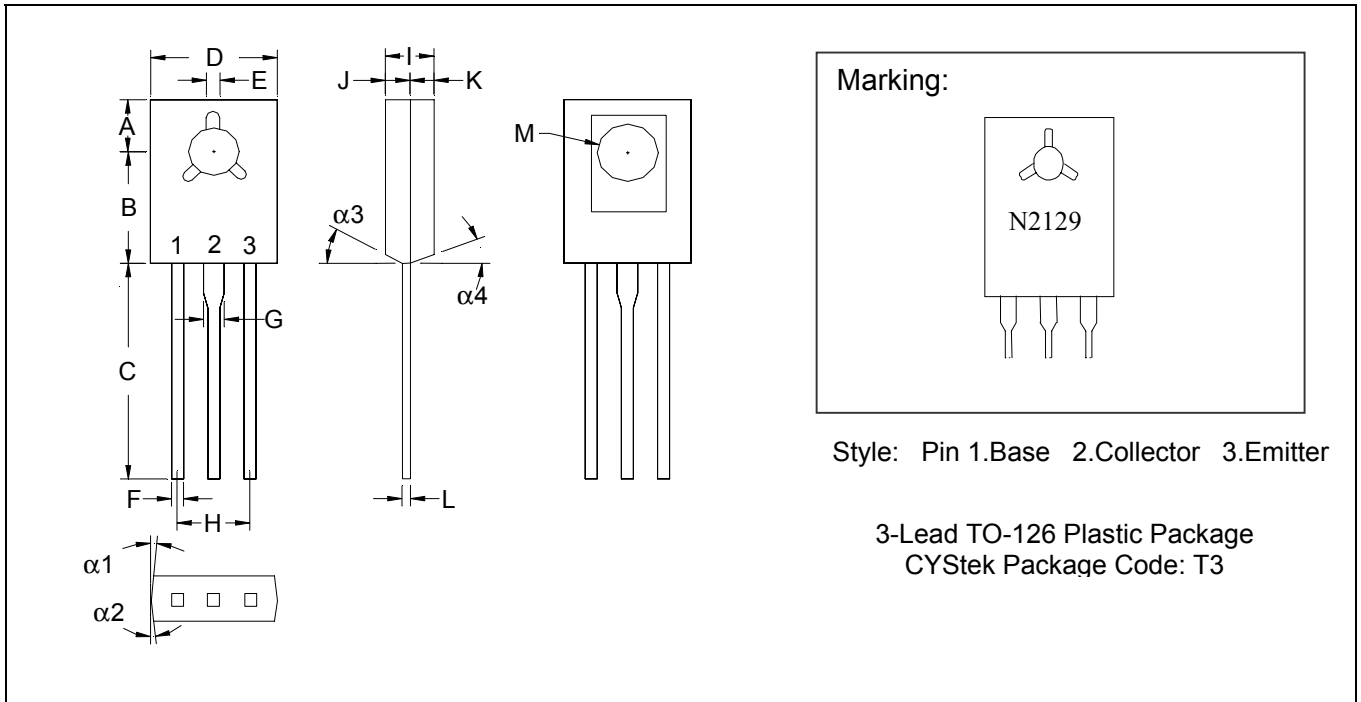
Power Derating Curve



Power Derating Curve



TO-126 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
$\alpha 1$	-	*3°	-	*3°	F	0.0280	0.0319	0.71	0.81
$\alpha 2$	-	*3°	-	*3°	G	0.0480	0.0520	1.22	1.32
$\alpha 3$	-	*3°	-	*3°	H	0.1709	0.1890	4.34	4.80
$\alpha 4$	-	*3°	-	*3°	I	0.0950	0.1050	2.41	2.66
A	0.1500	0.1539	3.81	3.91	J	0.0450	0.0550	1.14	1.39
B	0.2752	0.2791	6.99	7.09	K	0.0450	0.0550	1.14	1.39
C	0.5315	0.6102	13.50	15.50	L	-	*0.0217	-	*0.55
D	0.2854	0.3039	7.52	7.72	M	0.1378	0.1520	3.50	3.86
E	0.0374	0.0413	0.95	1.05					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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